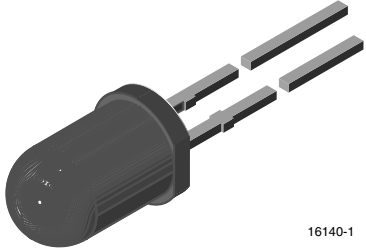


Silicon PIN Photodiode, RoHS Compliant



16140-1

DESCRIPTION

BPV10NF is a PIN photodiode with high speed and high radiant sensitivity in black, T-1 $\frac{3}{4}$ plastic package with daylight blocking filter. Filter bandwidth is matched with 870 nm to 950 nm IR emitters.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): $\varnothing$ 5
- Leads with stand-off
- Radiant sensitive area (in mm²): 0.78
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- High bandwidth: > 100 MHz at $V_R = 12$ V
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 20^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSFFxxxx series IR emitters

PRODUCT SUMMARY

COMPONENT	I_{ra} (mA)	φ (deg)	$\lambda_{0.5}$ (nm)
BPV10NF	60	± 20	790 to 1050

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPV10NF	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	215	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from body	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	350	K/W

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.0	1.3	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}$, $E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 20 \text{ V}$, $E = 0$	I_{ro}		1	5	nA
Diode capacitance	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, $E = 0$	C_D		11		pF
Open circuit voltage	$E_o = 1 \text{ mW/cm}^2$, $\lambda = 870 \text{ nm}$	V_O		450		mV
Short circuit current	$E_o = 1 \text{ mW/cm}^2$, $\lambda = 870 \text{ nm}$	I_K		50		μA
Reverse light current	$E_o = 1 \text{ mW/cm}^2$, $\lambda = 870 \text{ nm}$, $V_R = 5 \text{ V}$	I_{ra}		55		μA
	$E_o = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $V_R = 5 \text{ V}$	I_{ra}	30	60		μA
Temperature coefficient of I_{ra}	$E_o = 1 \text{ mW/cm}^2$, $\lambda = 870 \text{ nm}$, $V_R = 5 \text{ V}$	$TK_{I_{ra}}$		- 0.1		%/K
Absolute spectral sensitivity	$V_R = 5 \text{ V}$, $\lambda = 870 \text{ nm}$	$s(\lambda)$		0.55		A/W
Angle of half sensitivity		ϕ		± 20		deg
Wavelength of peak sensitivity		λ_p		940		nm
Range of spectral bandwidth		$\lambda_{0.5}$		790 to 1050		nm
Quantum efficiency	$\lambda = 950 \text{ nm}$	η		70		%
Noise equivalent power	$V_R = 20 \text{ V}$, $\lambda = 950 \text{ nm}$	NEP		3×10^{-14}		W/ $\sqrt{\text{Hz}}$
Detectivity	$V_R = 20 \text{ V}$, $\lambda = 950 \text{ nm}$	D^*		3×10^{12}		$\text{cm}^2/\text{Hz/W}$
Rise time	$V_R = 50 \text{ V}$, $R_L = 50 \text{ }\Omega$, $\lambda = 820 \text{ nm}$	t_r		2.5		ns
Fall time	$V_R = 50 \text{ V}$, $R_L = 50 \text{ }\Omega$, $\lambda = 820 \text{ nm}$	t_f		2.5		ns

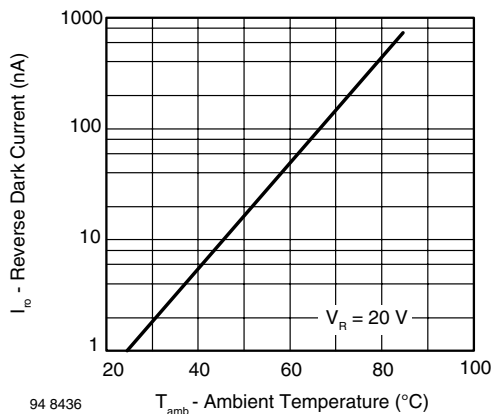
Note $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified**BASIC CHARACTERISTICS** $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

Fig. 1 - Reverse Dark Current vs. Ambient Temperature

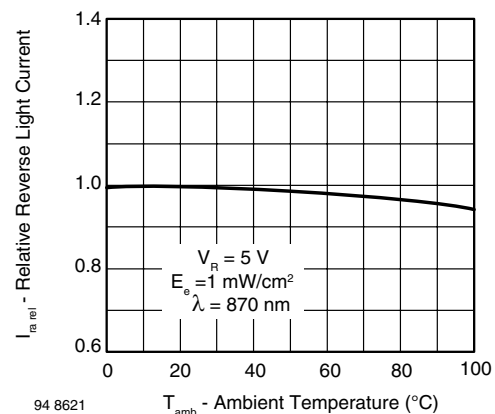


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

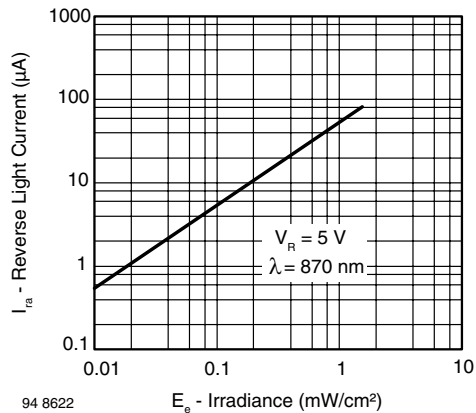


Fig. 3 - Reverse Light Current vs. Irradiance

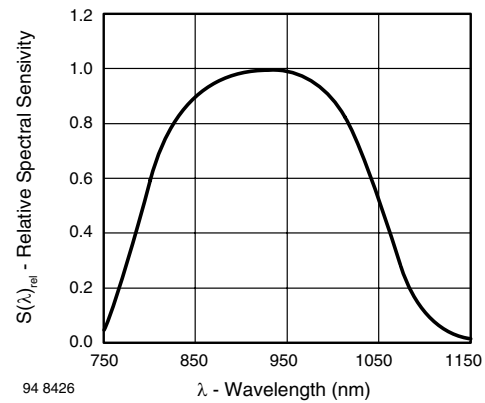


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

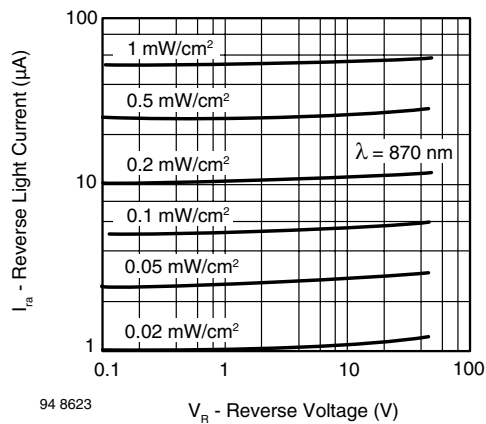


Fig. 4 - Reverse Light Current vs. Reverse Voltage

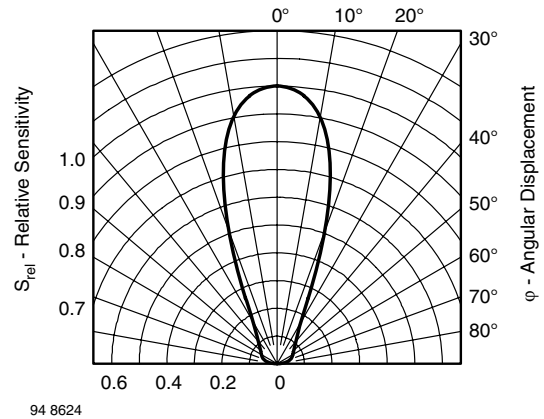


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

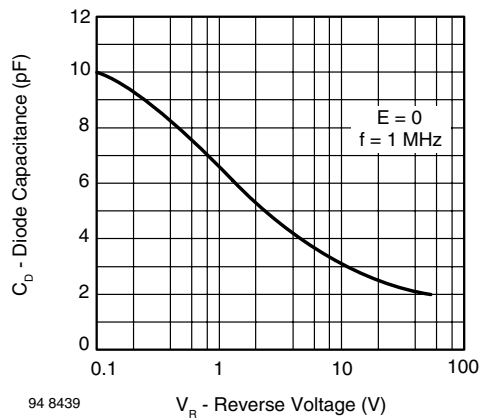
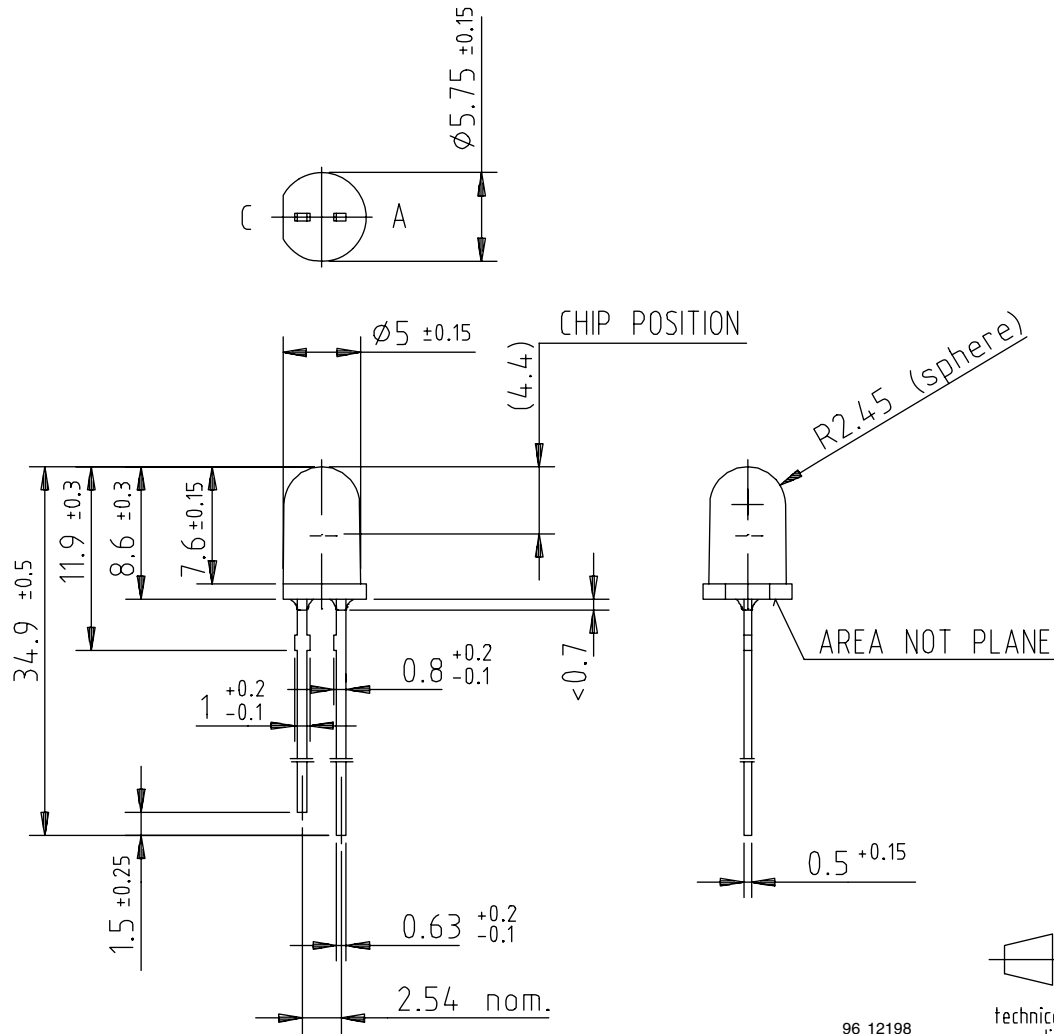
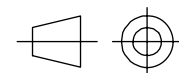


Fig. 5 - Diode Capacitance vs. Reverse Voltage

**PACKAGE DIMENSIONS** in millimeters

96 12198

technical drawings
according to DIN
specifications



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All product specifications and data are subject to change without notice.

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